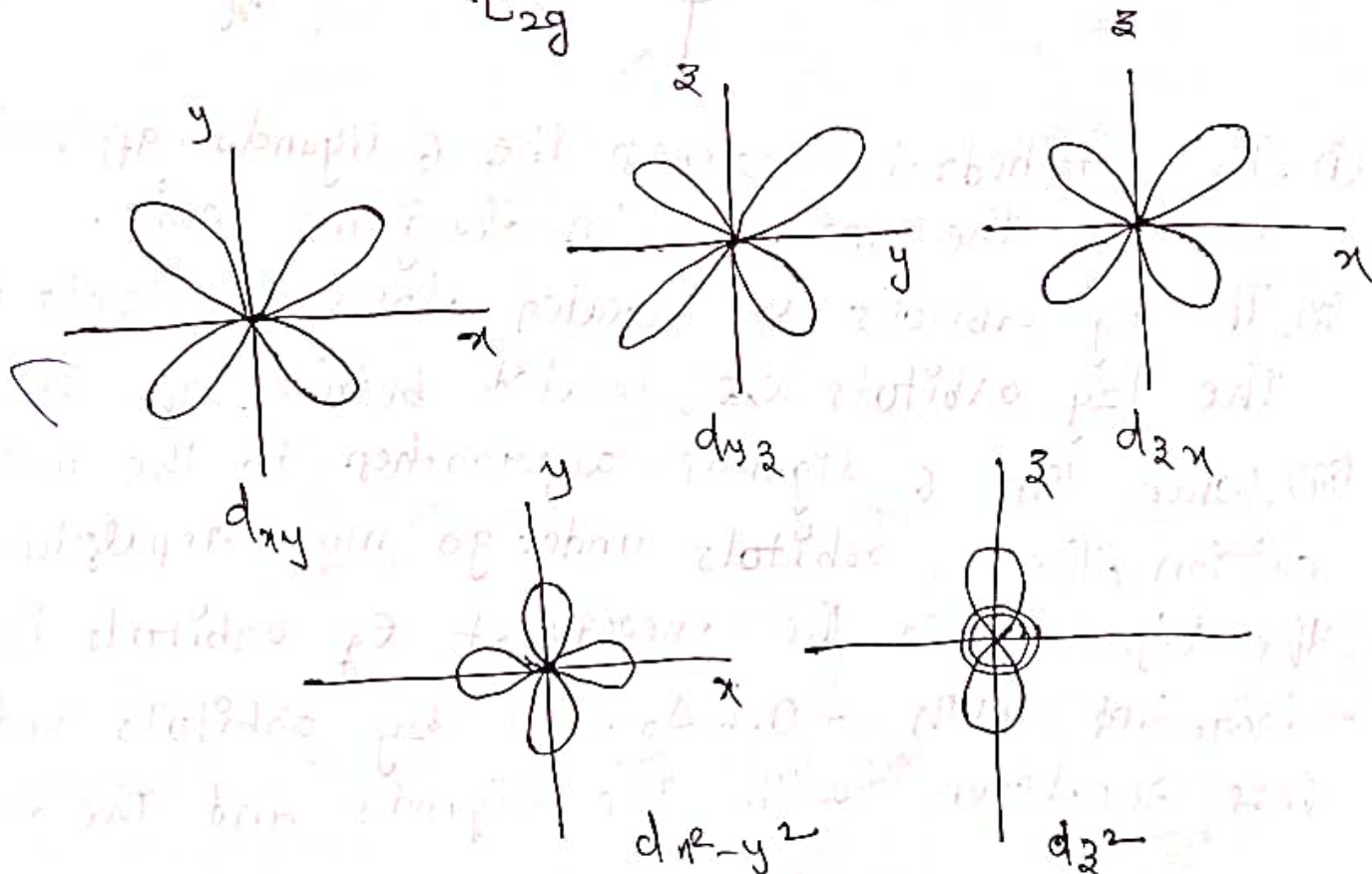
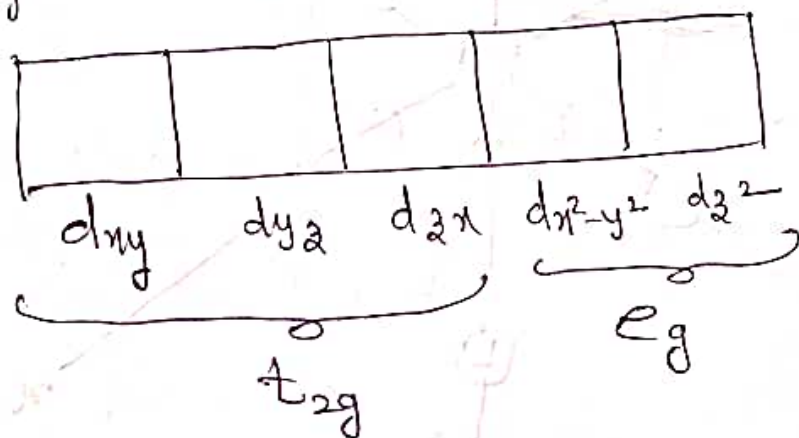


Modern Engineering Materials

Q. Write about crystal field theory?

Sol: CFT (Crystal Field Theory):-

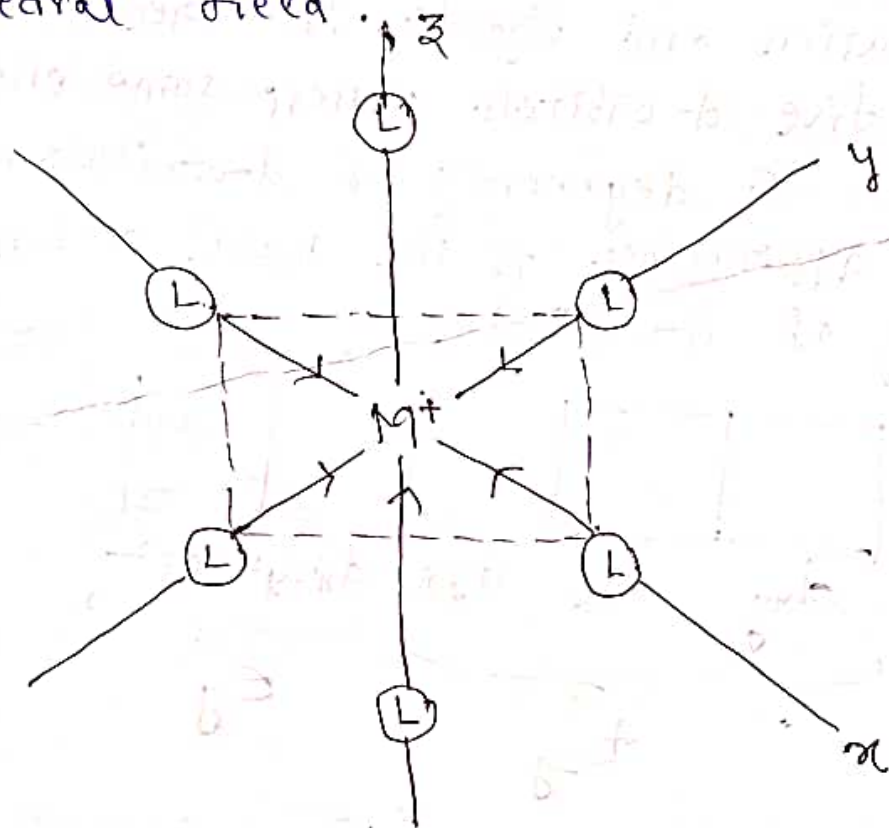
The CFT explains the splitting of d-orbitals which is due to the electrostatic field between metal cation and ligands. In free metal cation all the five d-orbitals possess same energy which is known as degeneracy of d-orbitals. When the ligands approach to the metal cation undergo splitting of d-orbitals.



The d_{xy} , d_{yz} , d_{zx} orbitals are called t_{2g} set of d-orbitals which are located between the axis. $d_{x^2-y^2}$, d_{z^2} orbitals are called e_g set of d-orbitals, which are located along the axis.

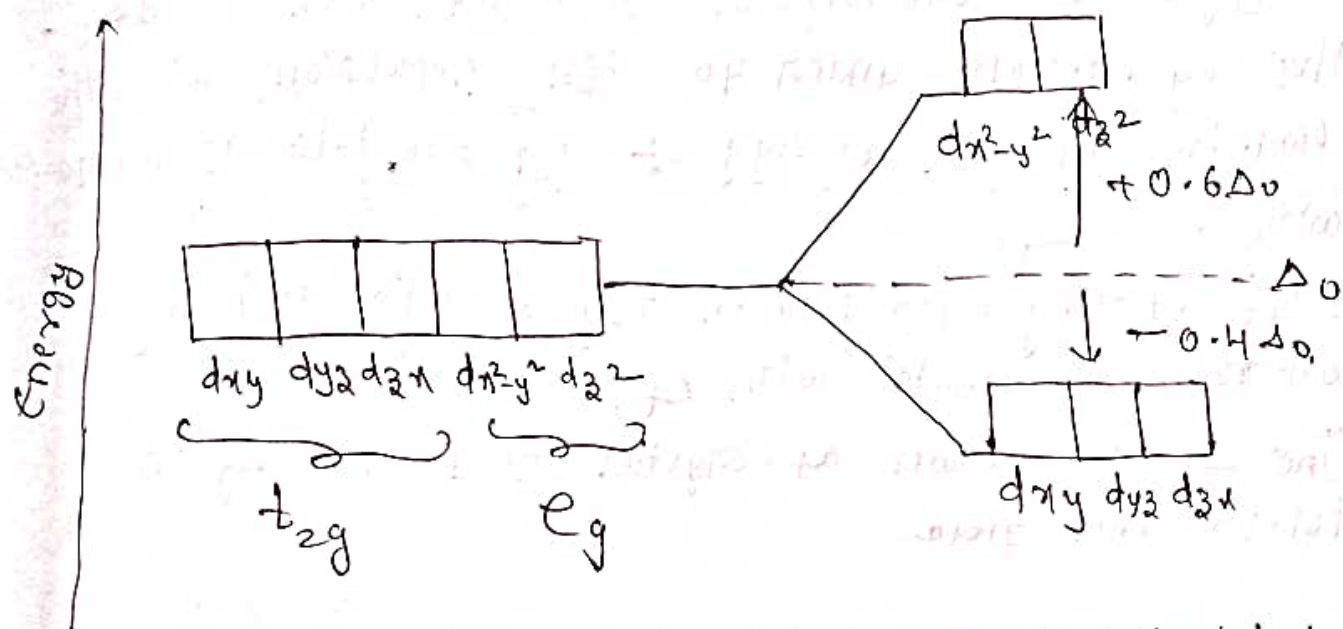
Q. Explain the splitting of d-orbitals in octahedral field.

Soln



- (i) In octahedral complexes the 6 ligands approach towards the metal cation along the axis.
- (ii) The e_g orbitals are located along the axis and the t_{2g} orbitals are located between the axis.
- (iii) When the 6 ligands approach to the metal cation, the e_g orbitals undergo more repulsion with the ligands and the energy of e_g orbitals is increased with $+0.6 \Delta_o$. The t_{2g} orbitals undergo less repulsion with the ligands and the energy

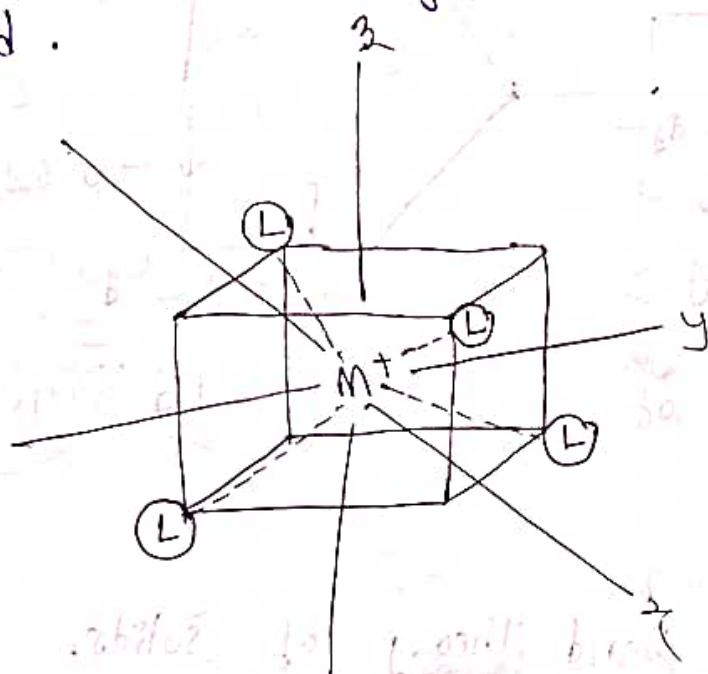
- of t_{2g} orbitals is decreased with $-0.4\Delta_o$.
- (iv). The energy gap between e_g orbitals and t_{2g} orbitals is denoted with Δ_o .
- (v). The Δ_o is known as crystal field splitting in octahedral field.



Splitting of d-orbitals in OH (Octahedral).

Q. Explain the splitting of d-orbitals in tetrahedral field.

Sol:-



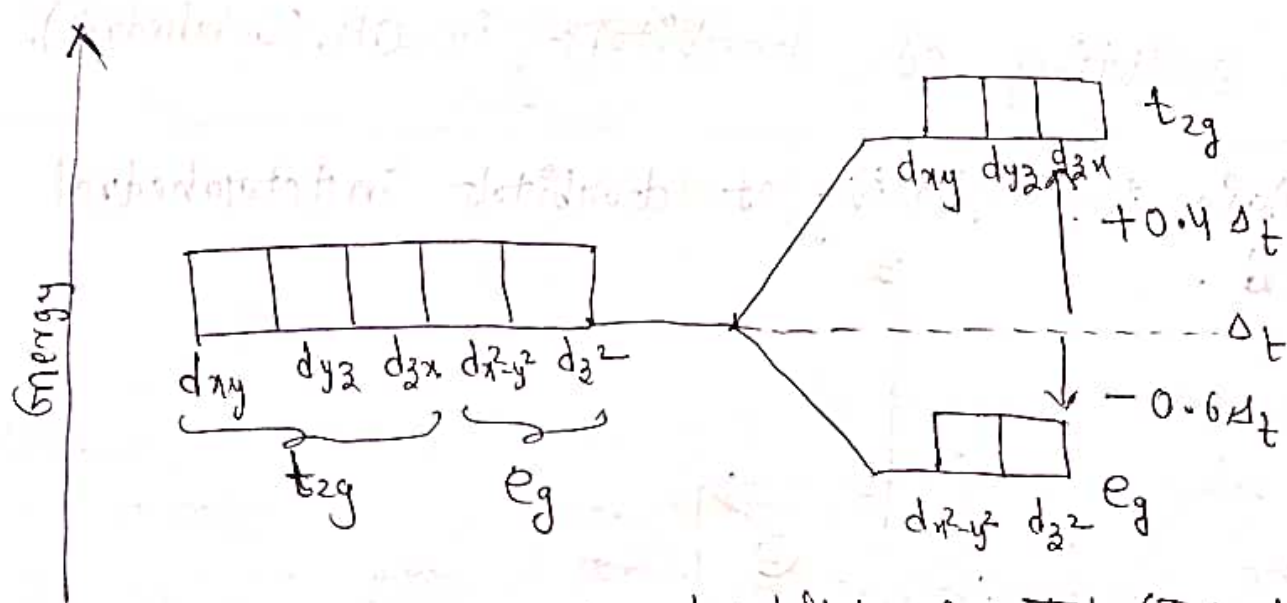
(i) In tetrahedral complex the four ligands approach towards the metal cation between the axis.

(i) The e_g orbitals are located along the axis and the t_{2g} orbitals are located b/w the axis.

(ii) When the four ligands ~~are located b/w the~~ approach to the metal cation the t_{2g} orbitals undergo more repulsion with the ligands and the energy of t_{2g} orbitals is increased with $+0.4\Delta_t$. The e_g orbitals undergo less repulsion with the ligands and the energy of e_g orbitals is decreased with $-0.6\Delta_t$.

(iv). The energy gap between t_{2g} orbitals and e_g orbitals is denoted with Δ_t .

(v) The Δ_t is known as crystal field splitting in tetrahedral field.



Splitting of d-orbitals in Td. (Tetrahedral)

Semi Conductors:-

①. Write a note on Band Theory of Solids.

Sol: In solid crystal lattice, the 'n' number of atoms are combined together as the atomic orbitals to form molecular orbitals. Which are

considered as energy levels.

The 'n' number of energy levels interact to form energy band. Thus energy band is a group of energy levels in a solid.

The energy band is classified into two types.

(i) Valency Band (ii) Conduction Band.

Valency Band:-

Valency band is a outermost band, which is filled with electrons.

Conduction Band:-

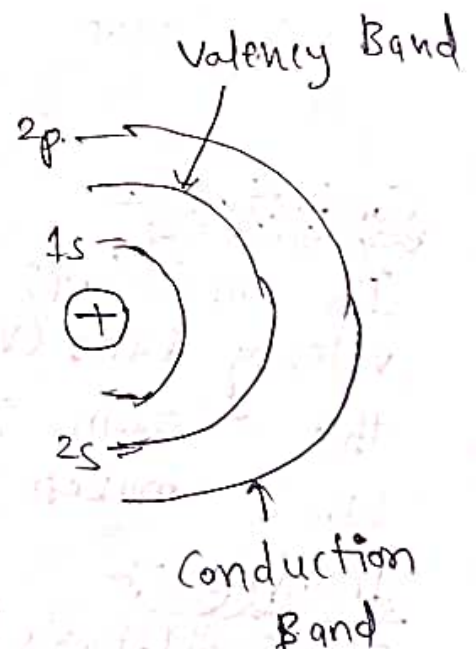
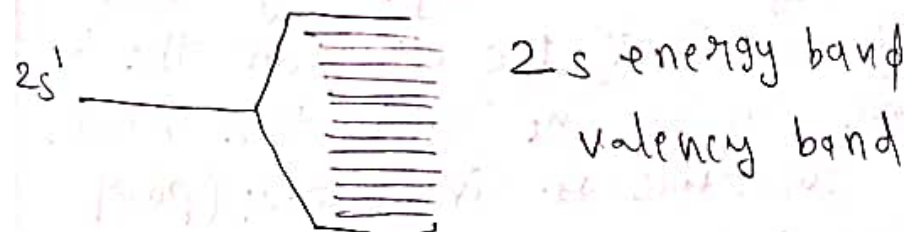
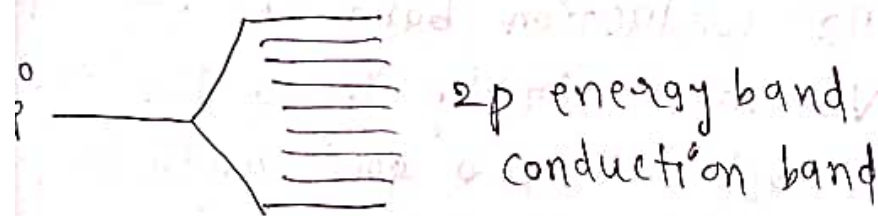
Conduction band is present above the valency band which is empty band.

Forbidden Gap (E_g):-

The energy gap between valency band and conduction band is known as forbidden gap.

Example:- Lithium crystal lattice.

$$EC = 1s^2 2s^1 2p^0$$

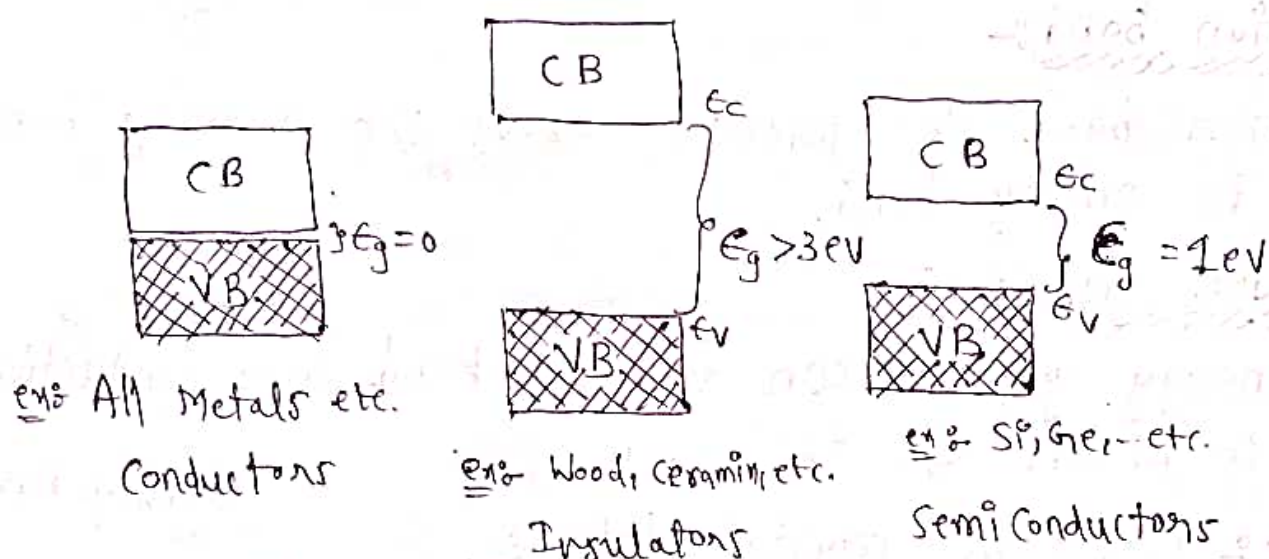


In lithium crystal lattice the e^- from valency band moves in to the conduction band which makes the substance a good conductor.

Q. Write the band diagram of conductors, insulators, semiconductors?

Sol: The solid substances are classified into three types based on the energy gap between valency band and conduction band.

(i) Conductors, (ii) Insulators, (iii) semiconductors.



Conductors:-

In conductors the energy gap is zero between valency band (VB) and conduction band (CB). So that the e^- from the VB move freely in to the CB. Which makes the substance as a good conductor.

Insulators:-

In insulators, the E_g is too large ($E_g > 3\text{eV}$) between VB and CB. So that the e^- from the VB are not able to move in to the conduction band. Which makes the substance as insulator (poor conductor of electricity).

Semi Conductors:-

In semi conductors the E_g is small ($E_g = 1\text{eV}$) between VB and CB. The semi conductors behave as both insulators and conductors. At absolute zero temperature (0°K) the semi conductors behave as insulators. At room temperature the semi conductors behave as conductors because at this temperature the e^- can break the covalent bond and come out as a free e^- which are enter into the CB.

Q. Write the effect of doping on semi conductors.

Ans. Explain the p-type and n-type semi conductors.

Sol. The semi conductors are two types.

(i) Intrinsic Semi Conductors.

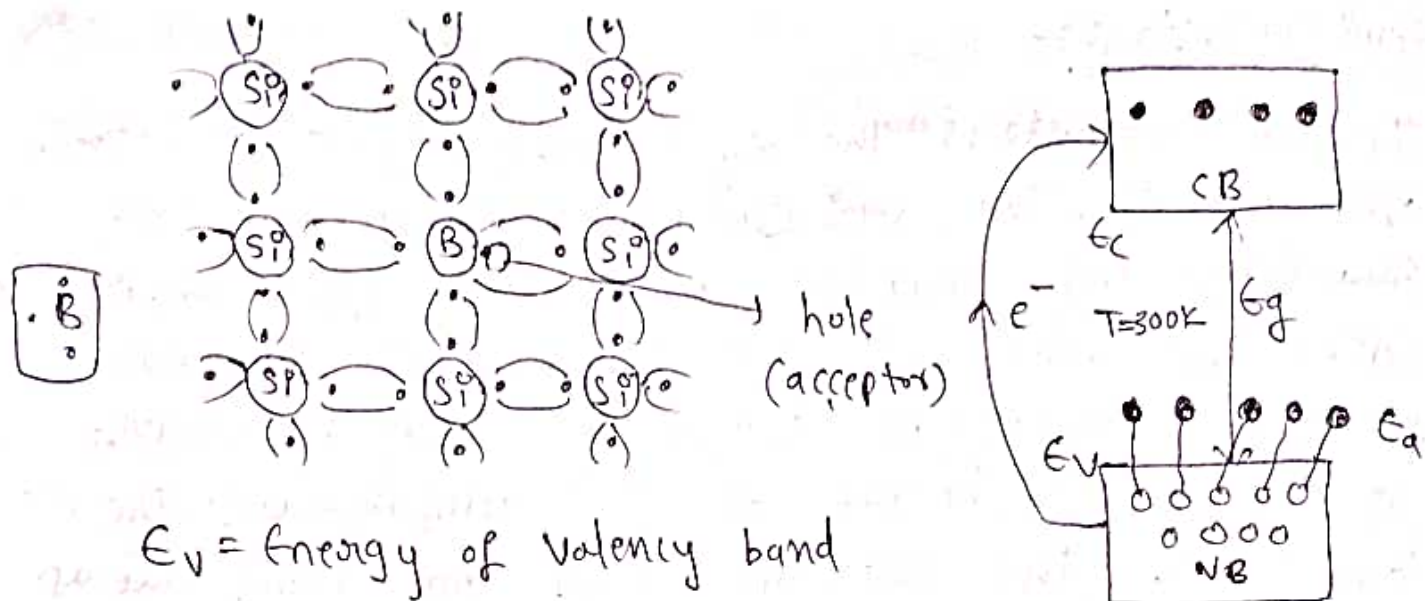
(ii) Extrinsic Semi Conductors.

The pure form of semi conductors are known as intrinsic semi conductor. The process of adding of impurities to the intrinsic semi conductor is known as doping, the doped SC's are called extrinsic semi conductors. The extrinsic SC are two types. based on the addition of type of impurities to the intrinsic SC.

(i) P-type SC (ii) N-type SC.

P-type SC:-

The addition of tri-valent impurities like B, Al, Ga to the intrinsic SC is called p-type SC.



E_v = Energy of Valency band

E_c = Energy of conduction band

E_a = accepting energy

In Si crystal lattice each Si atom forms four covalent bonds with surrounding Si atoms. When the addition of 'B' impurities to the Si crystal, the Si atom is replaced by boron (B) atom.

The B forms three covalent bonds with surrounding Si atoms and the 4th bond is incomplete with the deficiency of e^- , which creates a hole. The boron

is in the position to accept an e^- ; the ~~position~~ ~~to accept an e^-~~ holes are called acceptors.

The acceptor energy level (E_a) is closer to the VB.

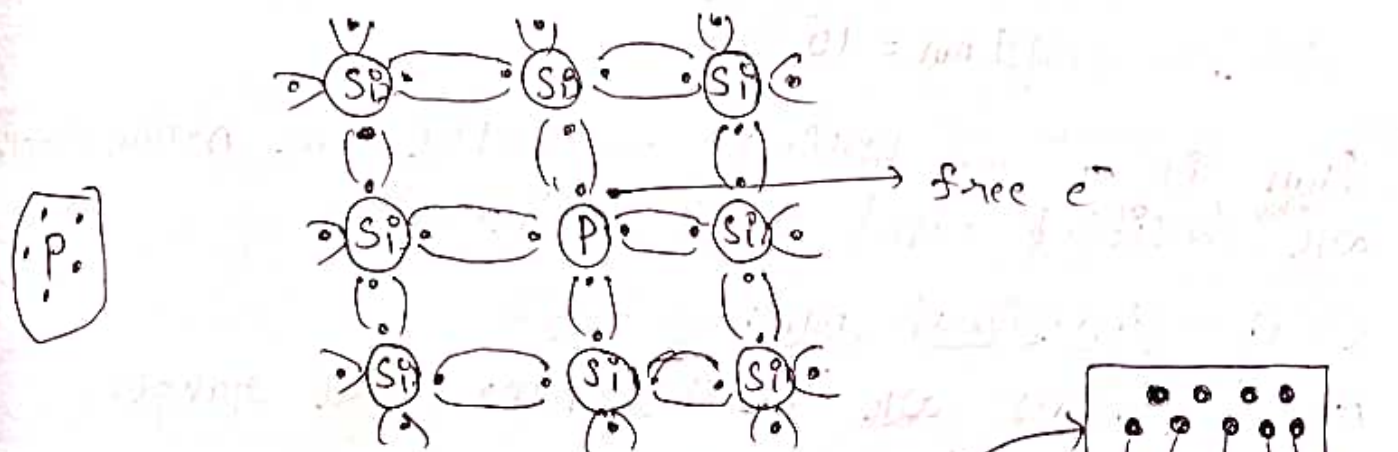
At $T > 0^\circ K$, the acceptors (holes) are accepting the e^- from the surrounding Si atoms and creating new holes in the VB.

At $T = 300K$, due to breakage of covalent bonds e^- move into the CB leaving holes in the VB. In p-type semi conductor the majority of charge carriers are holes and the minority of charge

carriers are electrons.

N-type Semiconductor

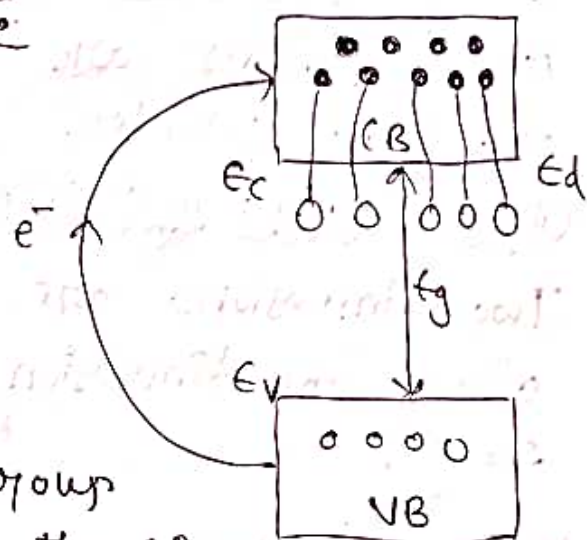
The addition of pentavalent impurities like P, As, Antimony to the intrinsic SC is known as n-type SC.



E_d = donor energy

E_c = Energy of CB

E_v = Energy of VB



When the addition of phosphorous impurities to the Si crystal, the Si atom is replaced by phosphorous atom. The 'P' has 5 valency e^- which forms 4 covalent bonds with surrounding Si atoms. and the 5th e^- on the 'P' is left as free e^- . The P is in the position to donate the e^- . The donor energy level is closer to the CB.

At $T > 0^\circ K$, the free electrons enter into the CB.

At $T = 300^\circ K$, due to the breakage of covalent bonds e^- move in the CB leaving holes in the VB.

In n-type SC the majority of charge carriers are e^- and the minority of charge carriers are holes.

Nanomaterials:-

The nano materials are defined as, the study of structures in the nano scale range. The nano scale range is 1nm to 100 nm.

$$1 \text{ nm} = 10^{-9} \text{ m}$$

1nm is a one billionth of metre. The nanomaterials are classified based on the dimensions.

(i) '0'-dimensional nanomaterials:-

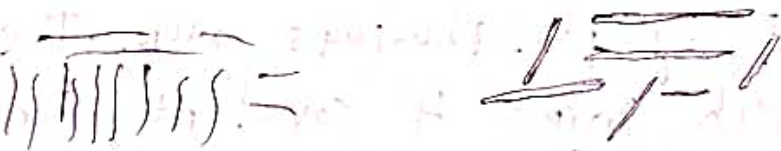
All dimensions are in the nano scale range.
ex: Nano particles.



(ii) 1-D, nano materials:-

Two dimensions are in the nano scale range other one dimension is not in the nano scale range.

ex: Nano wires, nano tubes



(iii) 2-D, nanomaterials:-

One dimension is in the nanoscale range the other two dimensions are not in the nanoscale range.

ex: Nanofilms, nano coating.

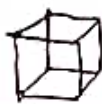


$\leq 100 \text{ nm}$

(iv) 3-D nanomaterials:-

No dimensions (x, y, z) in the nano scale range.

ex: Nano crystals.



Q Write a note on Graphene.

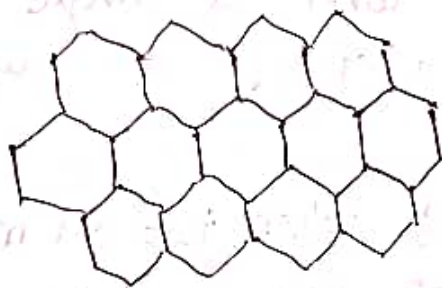
Ans: (i) Graphene is one of the allotropes of carbon.

(ii) A single layer of graphite is known as graphene.

(iii) In graphene each carbon atom is bonded with other three carbon atoms by strong covalent bonds.

(iv) In graphene all the carbon atoms are sp^2 hybridized.

(v) Graphene has 2-Dimensional hexagonal structure.



Graphene sheet.

Properties:-

(i) Graphene is the strongest, thinnest, flexible and light weight material.

(ii) Graphene is an excellent conductor.

Applications:-

(i) Graphene is used in high storage batteries and super charge batteries.

(ii) It is used in foldable displays of mobiles and laptops.

- (iii) It is used in concrete in construction.
- (iv) It is used as water filters.
- (v) It is used as anticorrosive agent for metals.

⑥ Write the properties and applications of carbon nano tubes (CNT's)?

Sol Carbon nano tubes are the allotropes of carbon. CNT are formed when graphene sheets are rolled up into a tube. CNT's are sp^2 hybridized CNT's has cylindrical structure. CNT's are classified into two types,

(i) Single walled CNT's

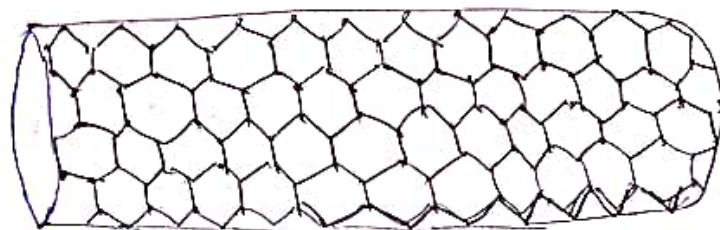
(ii) Multi walled CNT's

Single walled CNT's

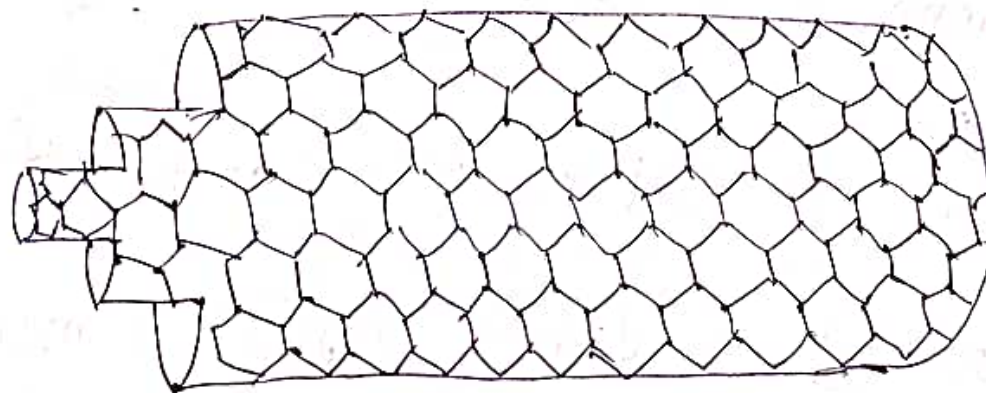
SWCNT's are formed when a single graphene sheets are rolled up into a tube.

Multi walled CNT's

MWCNT's are formed when two (or) more graphene sheets are rolled up into a tube.



SWCNT's



MWCNT's

Properties:-

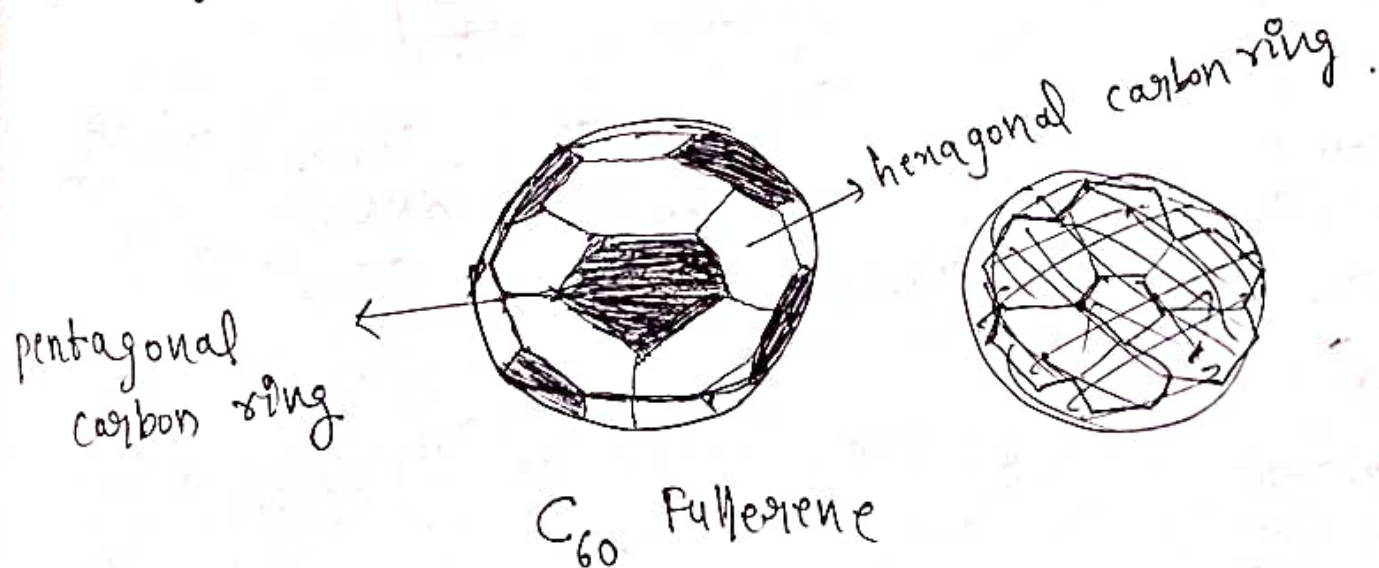
- (i) CNT's are the strongest and stiffest materials.
- (ii) CNT's have high electrical conductivity.
- (iii) CNT's have high thermal conductivity.
- (iv) CNT's have high flexibility.
- (v) CNT's have low thermal expansion.

Applications:-

- (i) CNT's are used in field emission transistors.
- (ii) CNT's are used in field emission light devices.
- (iii) CNT's are used in bio-sensors.
- (iv) CNT's are used in cancer therapy and drug delivery.
- (v) CNT's are used in energy storage batteries.

Q. Write the properties and applications of Fullerene.

sol:- Fullerene are the allotropes of carbon. It has hollow spherical structure. It was discovered by R. Buckminster Fuller, so that it is called Buckminster fullerene and it is short named as fullerene (or Bucky ball). The 'C' atoms are arranged in pentagonal and hexagonal manner.



Properties:-

- (i) Fullerenes acts as oxidizing agents.
- (ii) Fullerenes are unstable at higher temperature.
- (iii) C_{60} Fullerene is a very poor conductor of electricity but when reacts with alkalene it acts as super conductor.
- (iv) Heat of sublimation increases with increasing the size of fullerene.

Applications:-

- (i) Fullerenes are used in micro electronic devices.
- (ii) Fullerenes are used in micro electrical devices.
- (iii) Fullerenes are used in soft ferro-magnetic materials.
- (iv) Fullerenes are used in non-linear optical devices.
- (v) Fullerenes are used as super conductors.

